

B-2 Application of Nitride and Other Semiconductors

Representative Organizer

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Poster Session March 28 (Sat.) 16:45 ~ 18:00

- 16:45 B2-P-01 **Investigation of Dependence on Anode-Cathode Length of Reverse Breakdown Voltage of Five-2DEG-Channel Diodes Fabricated on Sapphire Substrate**
¹Akihisa Terano, ¹Tomonobu Tsuchiya, ¹Kazuhiro Mochizuki, ²Tohru Nakamura
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2 RESEARCH CENTER FOR MICRO-NANO TECHNOLOGY, HOSEI UNIVERSITY
- 16:45 B2-P-02 **The Drain Current Reduction Mechanism of Normally off AlGaIn/GaN HEMT on Si (111) by Recessed Gate**
¹Jyun-Hao Lin, ¹Shyh-Jer Huang, ¹Chao-Hsing Lai, ^{1,2}Yan-Kuin Su
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- 16:45 B2-P-03 **Investigation of Stress Time-Induced Electron Capture in AlGaIn/GaN HEMT on Si**
Tomotaka Narita, Yuki Katayama, Akio Wakejima, Takashi Egawa
RESEARCH CENTER FOR NANO-DEVICE AND SYSTEM, NAGOYA INSTITUTE OF TECHNOLOGY
- 16:45 B2-P-04 **AlGaIn/GaN HEMT with Distributed Gate Grown on Stripe Patterned Si (111)**
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- 16:45 B2-P-05L **Gigantic Enhancement on UV Photoresponse of Single Nonpolar a-Axial GaN Nanowire via Piezo-Phototronic Effect**
Chen-Yu Tsai, Chao-Hung Wang, Chung-Wei Chang, Chuan-Pu Liu
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